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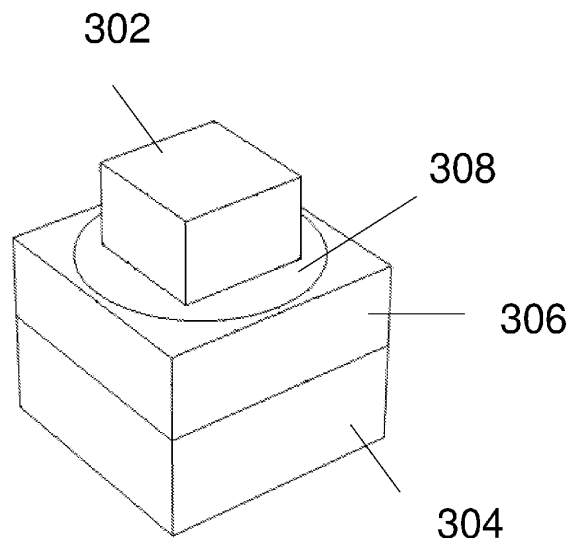
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(54) Title: ABSORBER AND METHOD OF FORMING THE SAME

FIG. 3



(57) Abstract: Various embodiments may relate to an absorber. The absorber may include a semiconductor absorption structure doped with dopants of a first conductivity type. The absorber may also include a semiconductor substrate doped with dopants of a second conductivity type different from the first conductivity type. The absorber may further include a dielectric layer between the semiconductor absorption structure and the semiconductor substrate. The absorber may additionally include a buried semiconductor structure included in a cavity of the dielectric layer, the buried semiconductor structure doped with dopants of the first conductivity type.

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